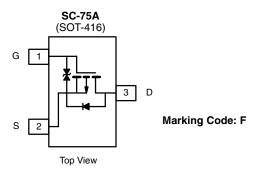




## P-Channel 60 V (D-S) MOSFET

| PRODUCT SUMMARY                        |                                 |                         |                     |  |
|--|---------------------------------|-------------------------|---------------------|--|
| $V_{DS(min.)}(V)$ $R_{DS(on)}(\Omega)$ |                                 | V <sub>GS(th)</sub> (V) | I <sub>D</sub> (mA) |  |
| - 60                                   | 4.0 at V <sub>GS</sub> = - 10 V | - 1 to 3.0              | - 190               |  |



Ordering Information: Si1021R-T1-GE3 (Lead (Pb)-free and Halogen-free)

### **FEATURES**





ROHS COMPLIANT HALOGEN FREE

- TrenchFET® Power MOSFETs
- · High-Side Switching
- Low On-Resistance: 4 Ω
- Low Threshold: 2 V (typ.)
- Fast Switching Speed: 20 ns (typ.)
- Low Input Capacitance: 20 pF (typ.)
- Miniature Package
- ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC

### **APPLICATIONS**

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- · Battery Operated Systems
- Power Supply Converter Circuits
- · Solid-State Relays

### **BENEFITS**

- · Ease in Driving Switches
- · Low Offset Voltage
- Low-Voltage Operation
- · High-Speed Circuits
- · Easily Driven without Buffer
- Small Board Area

| ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted) |                        |                                   |             |      |  |
|---|------------------------|-----------------------------------|-------------|------|--|
| Parameter   |                        | Symbol                            | Limit       | Unit |  |
| Drain-Source Voltage  |                        | V <sub>DS</sub>                   | - 60        | V    |  |
| Gate-Source Voltage   |                        | V <sub>GS</sub>                   | ± 20        | V    |  |
| Continuous Drain Current /T 150 °C\8                                      | T <sub>A</sub> = 25 °C |                                   | - 190       |      |  |
| Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>           | T <sub>A</sub> = 85 °C | l <sub>D</sub>                    | - 135       | mA   |  |
| Pulsed Drain Current <sup>b</sup>   |                        | I <sub>DM</sub>                   | - 650       |      |  |
| Power Dissipation <sup>a</sup>  | T <sub>A</sub> = 25 °C | В                                 | 250         | mW   |  |
| Power Dissipation   | T <sub>A</sub> = 85 °C | P <sub>D</sub>                    | 130         | ]    |  |
| Maximum Junction-to-Ambient <sup>a</sup>                                  |                        | R <sub>thJA</sub>                 | 500         | °C/W |  |
| Operating Junction and Storage Temperature Range                          |                        | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 150 | °C   |  |

#### Notes:

- a. Surface mounted on FR4 board.
- b. Pulse width limited by maximum junction temperature.

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| <b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted) |                     |  |       |       |       |               |  |
|--|---------------------|--|-------|-------|-------|---------------|--|
| Parameter  | Symbol              | Test Conditions  | Min.  | Тур.  | Max.  | Unit          |  |
| Static   |                     |  |       |       |       |               |  |
| Drain-Source Breakdown Voltage   | V <sub>DS</sub>     | $V_{GS} = 0 \text{ V}, I_{D} = -10 \mu\text{A}$                                | - 60  |       | V     |               |  |
| Gate-Threshold Voltage   | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}, I_{D} = -0.25 \text{ mA}$                                    | - 1   |       | - 3.0 | V             |  |
|  |                     | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$                              |       |       | ± 10  | μΑ            |  |
| Gate-Body Leakage  | Lance               | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$                              |       | ± 200 |       |               |  |
| Gale-Body Leakage  | I <sub>GSS</sub>    | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$ |       |       | ± 500 | nA            |  |
|  |                     | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$                               |       |       | ± 100 |               |  |
| Zara Cata Valtaga Drain Current  |                     | V <sub>DS</sub> = - 50 V, V <sub>GS</sub> = 0 V                                |       |       | - 25  | - 25<br>- 250 |  |
| Zero Gate Voltage Drain Current  | I <sub>DSS</sub>    | V <sub>DS</sub> = - 50 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C        |       |       | - 250 |               |  |
| On State Drain Correcti  |                     | V <sub>DS</sub> = -10 V, V <sub>GS</sub> = - 4.5 V                             | - 50  |       |       | mA            |  |
| On-State Drain Current <sup>a</sup>                                    | I <sub>D(on)</sub>  | V <sub>DS</sub> = -10 V, V <sub>GS</sub> = - 10 V                              | - 600 |       |       |               |  |
| Drain-Source On-State Resistance <sup>a</sup>                          |                     | V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 25 mA                            |       |       | 8     | 8             |  |
|  | R <sub>DS(on)</sub> | V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 500 mA                            |       |       | 4 Ω   |               |  |
|  |                     | V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 500 mA, T <sub>J</sub> = 125 °C   |       |       | 6     | †             |  |
| Forward Transconductance   | 9 <sub>fs</sub>     | V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 100 mA                            | 80    |       |       | mS            |  |
| Diode Forward Voltage <sup>a</sup>                                     | V <sub>SD</sub>     | V <sub>DS</sub> = - 200 mA, V <sub>GS</sub> = 0 V                              | 80    |       |       | V             |  |
| Dynamic  |                     |  |       |       |       |               |  |
| Total Gate Charge  | Qg                  |  |       | 1.7   |       | nC            |  |
| Gate-Source Charge   | Q <sub>gs</sub>     | $V_{DS} = -30 \text{ V}, V_{GS} = -15 \text{ V}, I_{D} \cong -500 \text{ mA}$  |       | 0.26  |       |               |  |
| Gate-Drain Charge  | Q <sub>gd</sub>     |  |       | 0.46  |       |               |  |
| Input Capacitance  | C <sub>iss</sub>    |  |       | 23    |       |               |  |
| Output Capacitance   | C <sub>oss</sub>    | $V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$              |       | 10    |       | pF            |  |
| Reverse Transfer Capacitance   | C <sub>rss</sub>    |  |       | 5     |       |               |  |
| Switching <sup>b</sup>   |                     |  |       |       |       |               |  |
| Turn-On Time   | t <sub>ON</sub>     | V <sub>DD</sub> = - 25 V, R <sub>L</sub> = 150 Ω,                              |       | 20    |       | ns            |  |
| Turn-Off Time  | t <sub>OFF</sub>    | $I_D \cong$ - 200 mA, $V_{GEN} =$ - 10 V, $R_g =$ 10 $\Omega$                  |       | 35    |       |               |  |

### Notes:

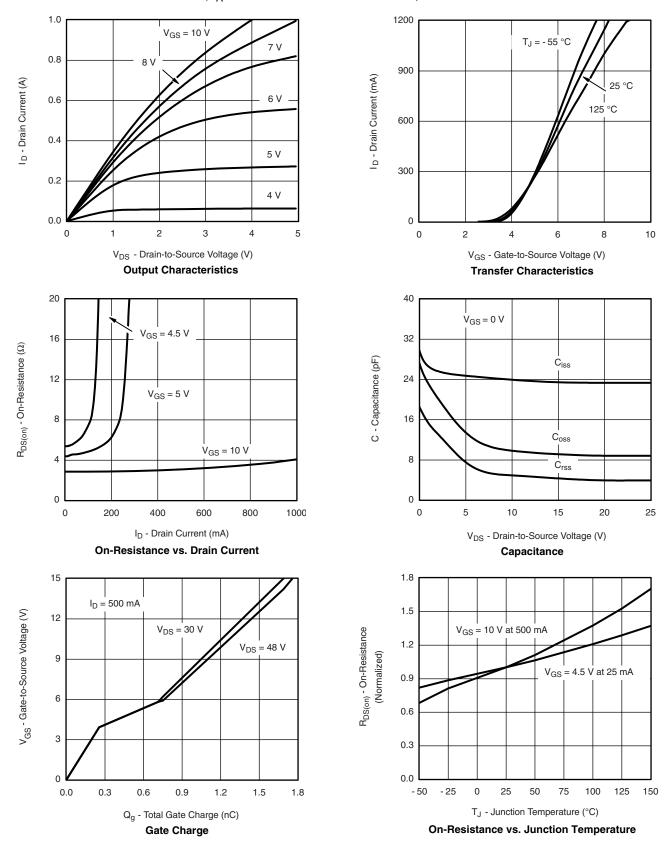
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.

b. Switching time is essentially independent of operating temperature.



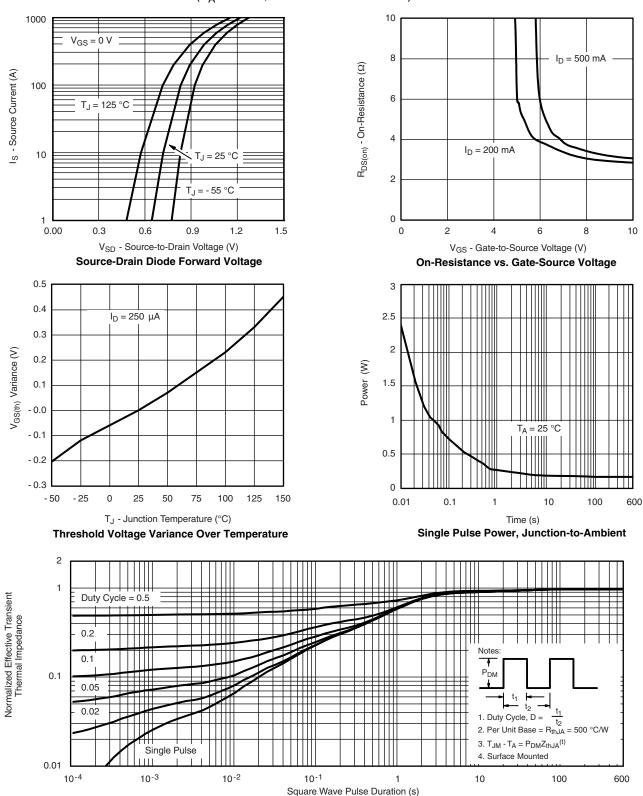
## **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)



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### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

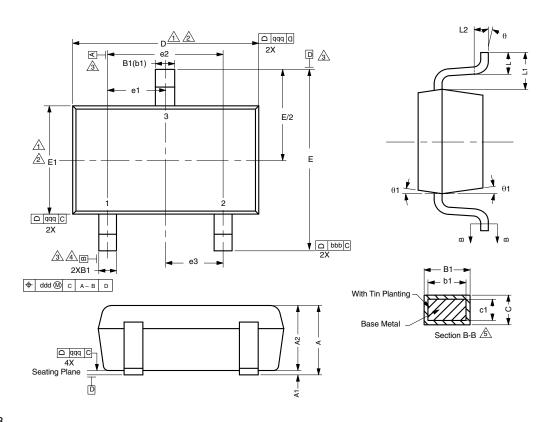


Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?71410">www.vishay.com/ppg?71410</a>.



## SC-75A: 3 Leads



DWG: 5868

#### Notes

Dimensions in millimeters will govern.

- Dimension D does not include mold flash, protrusions or gate burrs. Mold flash protrusions or gate burrs shall not exceed 0.10 mm per end. Dimension E1 does not include Interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.10 mm per side.
- Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.
- ②Datums A, B and D to be determined 0.10 mm from the lead tip.

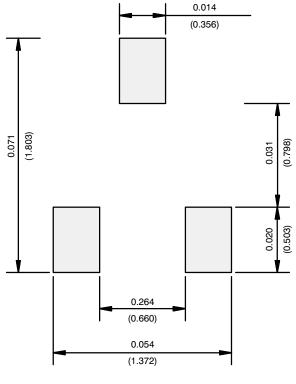
  4\text{Terminal positions are shown for reference only.}
- These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

| DIMENSIONS | TOLERANCES |  |  |
|------------|------------|--|--|
| aaa        | 0.10       |  |  |
| bbb        | 0.10       |  |  |
| ccc        | 0.10       |  |  |
| ddd        | 0.10       |  |  |

| DIM.   | MILLIMETERS |       |      | NOTE |
|--------|-------------|-------|------|------|
| DIIVI. | MIN.        | NOM.  | MAX. | NOTE |
| Α      | -           | -     | 0.80 |      |
| A1     | 0.00        | -     | 0.10 |      |
| A2     | 0.65        | 0.70  | 0.80 |      |
| B1     | 0.19        | -     | 0.24 | 5    |
| b1     | 0.17 - 0.21 |       | 0.21 |      |
| С      | 0.13        | -     | 0.15 | 5    |
| c1     | 0.10        | -     | 0.12 | 5    |
| D      | 1.48        | 1.575 | 1.68 | 1, 2 |
| E      | 1.50        | 1.60  | 1.70 |      |
| E1     | 0.66        | 0.76  | 0.86 | 1, 2 |
| e1     | 0.50 BSC    |       |      |      |
| e2     | 1.00 BSC    |       |      |      |
| e3     | 0.50 BSC    |       |      |      |
| L      | 0.15        | 0.205 | 0.30 |      |
| L1     | 0.40 ref.   |       |      |      |
| L2     | 0.15 BSC    |       |      |      |
| q      | 0°          | -     | 8°   |      |
| q1     | 4°          | -     | 10°  |      |



### **RECOMMENDED MINIMUM PADS FOR SC-75A: 3-Lead**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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